

# MMBD914

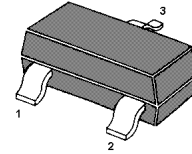
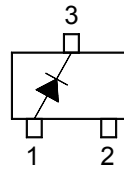
## Silicon Epitaxial Planar Switching Diode

### Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

### Applications

- Ultra high speed switching application



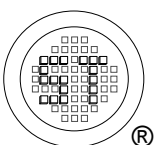
Marking Code: **5D**  
TO-236 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	100	V
Forward Current	$I_F$	200	mA
Non-repetitive Peak Forward Surge Current ( $t = 1\text{ }\mu\text{s}$ )	$I_{FSM}$	4	A
Power Dissipation	$P_{tot}$	350	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	$V_F$	-	1	V
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	100	-	V
Reverse Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$	$I_R$	-	25 5	nA $\mu\text{A}$
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$	$t_{rr}$	-	4	ns
Total Capacitance at $V_R = 0$ , $f = 1\text{ MHz}$	$C_T$	-	4	pF



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ISO/TS 16949 : 2009  
Certificate No. 160713000

ISO14001 : 2004  
Certificate No. 7116

ISO 9001 : 2008  
Certificate No. 90719410

BS-OHSAS 18001 : 2007  
Certificate No. 7116

IECQ QC 080000  
Certificate No. PRC-SP16-1485

Dated : 16/03/2015 Rev:01

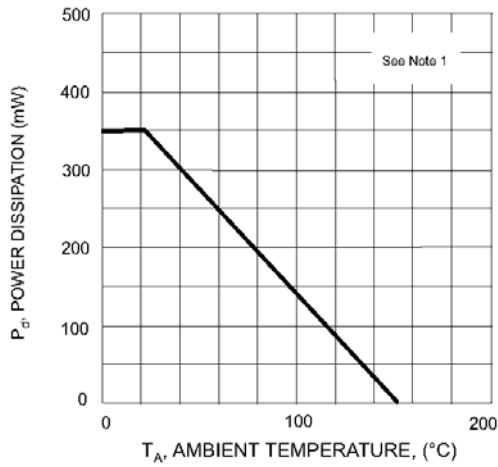


Fig. 1 Power Derating Curve

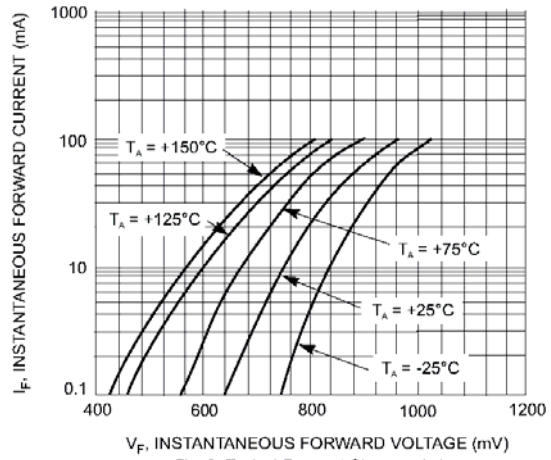


Fig. 2 Typical Forward Characteristics

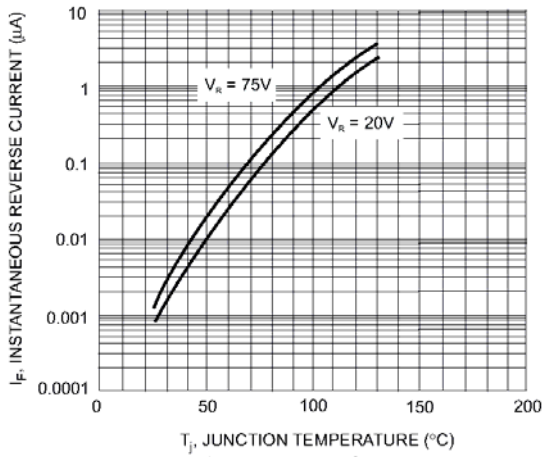
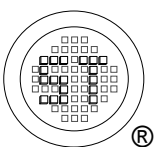


Fig. 3 Typical Reverse Characteristics



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